

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

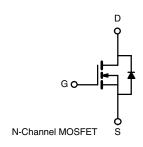
PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0095				
I _D (A)	120				
Configuration	Single				
Package	TO-220				



FEATURES

- TrenchFET® power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified ^d
- 100 % $\rm R_g$ and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATINGS	S (T _C = 25 °C, unless	s otherwise noted	i)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	T _C = 25 °C ^a	I-	120	
Continuous Drain Current	T _C = 125 °C	ID	73	
Continuous Source Current (Diode Conduction	on) ^a	I _S	120	A
Pulsed Drain Current ^b		I _{DM}	480	
Single Pulse Avalanche Current	le Pulse Avalanche Current L = 0.1 mH		73	
Single Pulse Avalanche Energy	L = 0.1 mm	E _{AS}	266	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	PD	375	W
	T _C = 125 °C	' D	125	vv
Operating Junction and Storage Temperature Range		TJ, T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	0/10	

- Notes
- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

1

SQP120N10-09



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	-				-		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS}	= 0, I _D = 250 μA	100	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 100 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-	-	150	1
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	Α
		V _{GS} = 10 V	I _D = 30 A	-	0.0079	0.0095	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0190	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0250	1
Forward Transconductance ^b	g _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	99	-	S
Dynamic ^b					•		
Input Capacitance	C _{iss}			-	6915	8645	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 V$, f = 1 MHz	-	635	795	pF
Reverse Transfer Capacitance	C _{rss}			-	280	350	
Total Gate Charge ^c	Qg			-	120	180	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, \text{ I}_{D} = 85 \text{ A}$	-	30	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	28.5	-	1
Gate Resistance	R _g		f = 1 MHz	0.25	0.7	2.3	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	21	32	
Rise Time ^c	t _r		$V_{DD} = 50 \text{ V}, \text{ R}_1 = 0.6 \Omega$		24	36	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 85 \text{ Å}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 2.5 \Omega$		-	52	78	
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	480	Α
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0		-	0.9	1.5	V

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

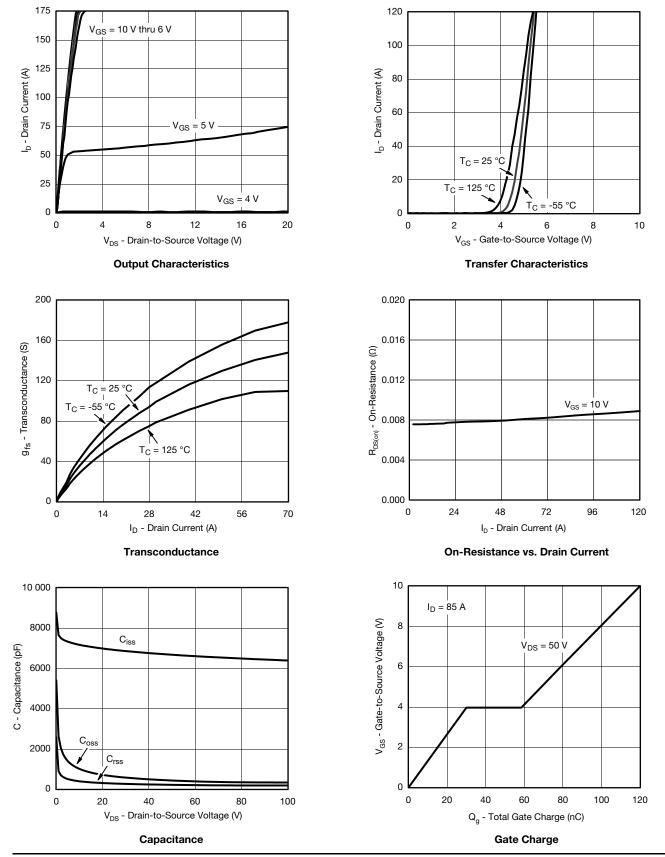
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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3

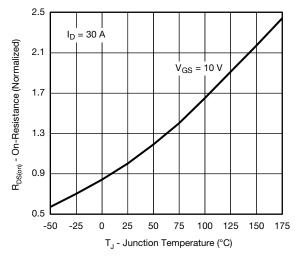
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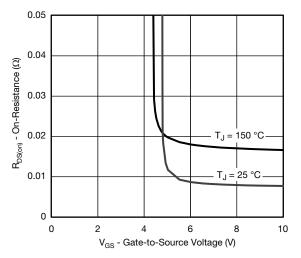
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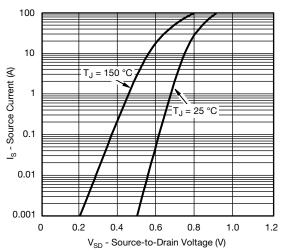
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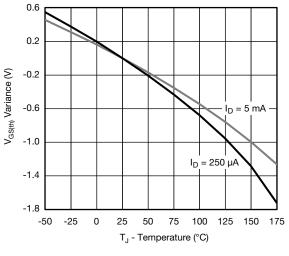
On-Resistance vs. Junction Temperature



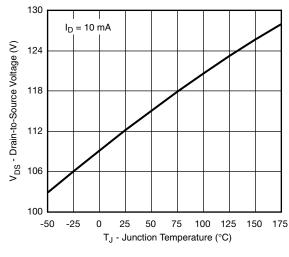
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature 4

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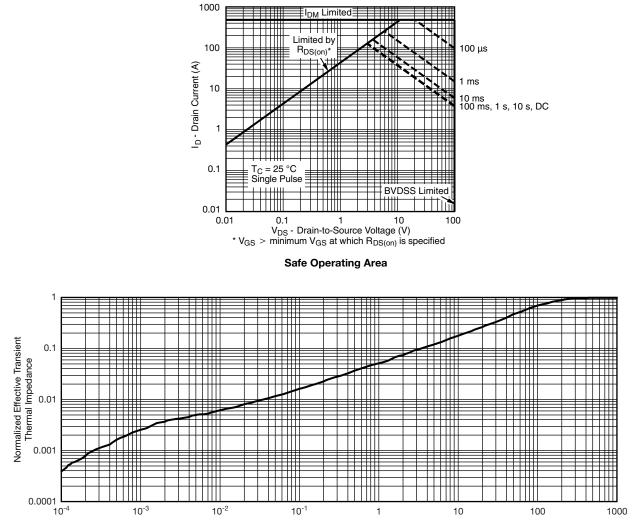
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

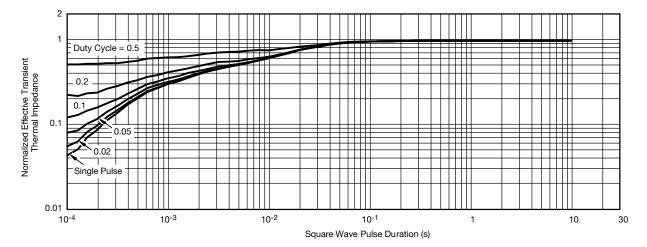


Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62663.



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REVISION HISTORY ^a			
REVISION	DATE	DESCRIPTION OF CHANGE	
В	04-Aug-15	Revised R _g minimum limit	

Note

a. As of April 2014



TO-220AB



	MILLIMETERS		INC	HES
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØР	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
	0413-Rev. P,		0.102	0.118

Note

 * M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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